

# PSMN7R6-60PS

# N-channel 60 V 7.8 m $\Omega$ standard level MOSFET Rev. 03 — 28 October 2010

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel MOSFET in a TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

#### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Hnit
Symbol	raiaiiietei	Conditions	IVIIII	Тур	IVIAX	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	60	V
$I_D$	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	-	92	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	149	W
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 13}}{\text{Figure 9}};$	-	5.9	7.8	mΩ
Dynamic ch	naracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 30 \text{ V}; \text{ see } \underline{\text{Figure 15}};$ see $\underline{\text{Figure 14}}$	-	10.6	-	nC
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 92 A; $V_{sup}$ ≤ 100 V; $R_{GS}$ = 50 Ω; unclamped	-	-	110	mJ



## **Pinning information**

Table 2. **Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

#### **Ordering information** 3.

Table 3. **Ordering information** 

Type number	Package		
	Name	Description	Version
PSMN7R6-60PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

# **Limiting values**

**Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	60	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	60	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	-	65	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	-	92	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; see <u>Figure 3</u>	-	389	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	149	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	92	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25  ^{\circ}C$	-	389	Α
Avalanche r	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 92 A; $V_{sup} \le$ 100 V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	110	mJ

PSMN7R6-60PS

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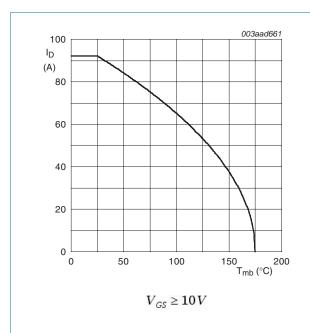


Fig 1. Continuous drain current as a function of mounting base temperature

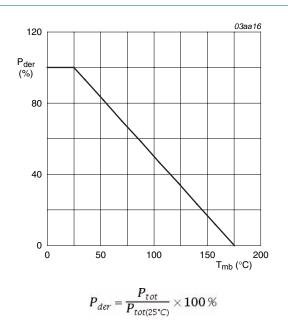
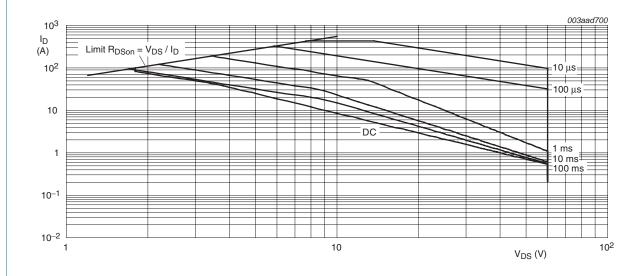


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25 \,{}^{\circ}C; I_{DM}$  is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## **Thermal characteristics**

Table 5. **Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	0.49	1.01	K/W

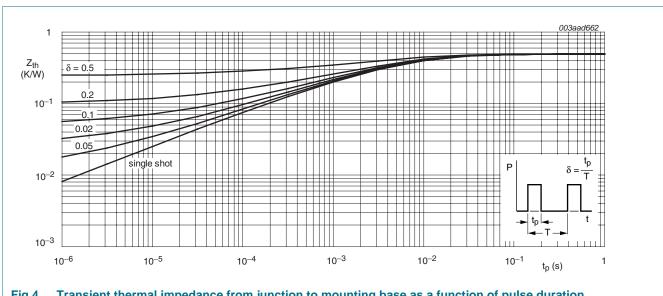


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

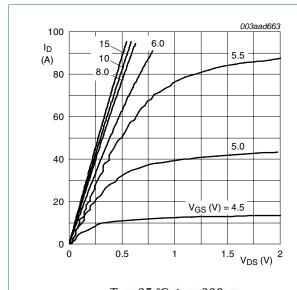
## 6. Characteristics

Table 6. Characteristics

Table 6.	Devenuetor	Conditions	N#!	T	NA	11!4
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; see <u>Figure 11</u>	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 11	-	-	4.6	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 125 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_i = 25 \text{ °C}$	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A; } T_j = 175 \text{ °C;}$ see <u>Figure 12</u>	-	13.3	18	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 13</u> ; see <u>Figure 9</u>	-	5.9	7.8	mΩ
$R_{G}$	gate resistance	f = 1 MHz	-	0.98	-	Ω
Dynamic o	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$	-	38.7	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 14; see Figure 15	-	12.9	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	6.9	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	6	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 30 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 15; see Figure 14	-	10.6	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 30 V; see <u>Figure</u> 14; see <u>Figure 15</u>	-	5.6	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 16}}{\text{Figure 8}}; \text{ see}$	-	2651	-	pF
C <sub>oss</sub>	output capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{\text{ Composition}}$	-	342	-	pF
C <sub>rss</sub>	reverse transfer capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 16}}{\text{Figure 8}}; \text{ see}$	-	183	-	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	19	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	21	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	37	-	ns
t <sub>f</sub>	fall time		-	13	-	ns

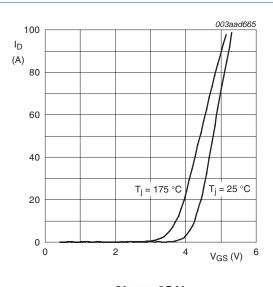
Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	in diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.86	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = 100 \text{ A/}\mu\text{s}$ ;	-	40.4	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}$	-	56	-	nC



 $T_i = 25$  °C;  $t_p = 300 \, \mu s$ 





 $V_{DS} = 25 \text{ V}$ 

Transfer characteristics: drain current as a

function of gate-source voltage; typical values

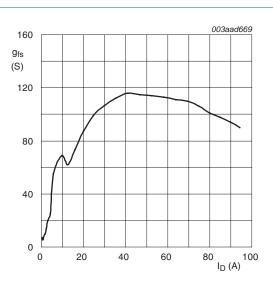


Fig 6. Forward transconductance as a function of drain current; typical values

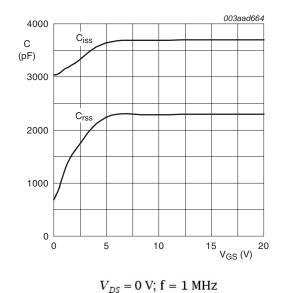


Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

Fig 7.

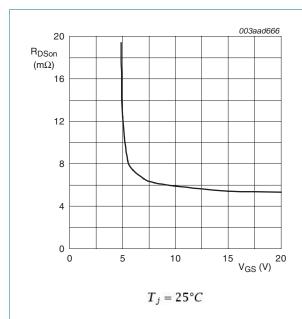


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

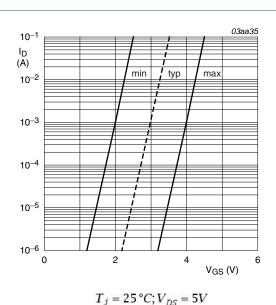


Fig 10. Sub-threshold drain current as a function of gate-source voltage

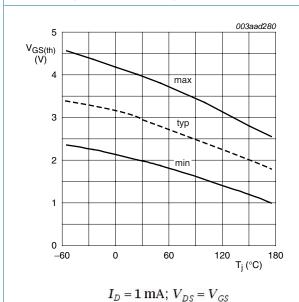


Fig 11. Gate-source threshold voltage as a function of junction temperature

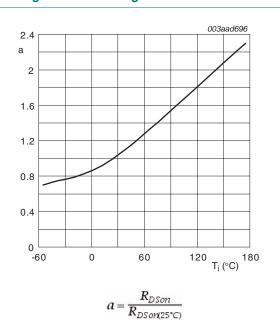


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature.

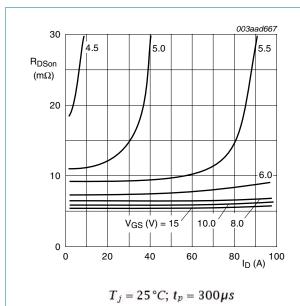
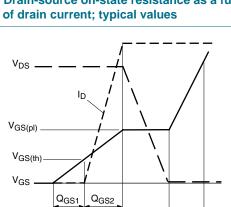


Fig 13. Drain-source on-state resistance as a function

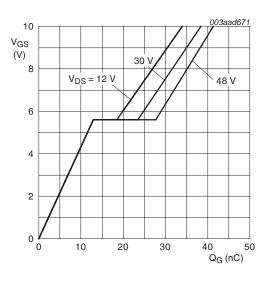


←Q<sub>GD</sub>− Q<sub>G(tot)</sub>

003aaa508

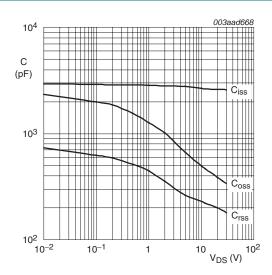
Fig 15. Gate charge waveform definitions

Q<sub>GS</sub>



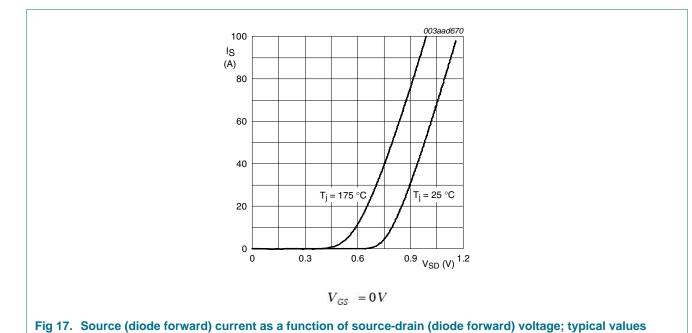
$$T_j = 25^{\circ}C; I_D = 25 A$$

Fig 14. Gate-source voltage as a function of gate charge; typical values

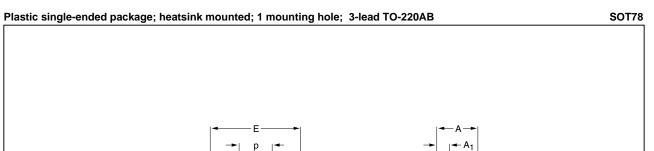


$$V_{DS} = 0V$$
;  $f = 1 \text{ MHz}$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical



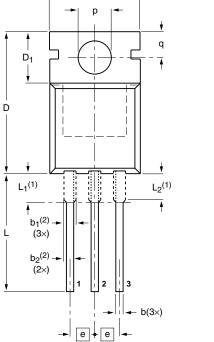
## 7. Package outline

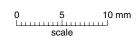


mounting

base

Q





#### **DIMENSIONS (mm are the original dimensions)**

UNI	T A	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> (1)	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q	
mn	1 4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2	

#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

Fig 18. Package outline SOT78 (TO-220AB)

PSMN7R6-60PS

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## 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R6-60PS v.3	20101028	Product data sheet	-	PSMN7R6-60PS v.2
Modifications:	<ul> <li>Various changes t</li> </ul>	o content.		
PSMN7R6-60PS v.2	20100122	Product data sheet	-	-

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#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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#### N-channel 60 V 7.8 mΩ standard level MOSFET

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# PSMN7R6-60PS

## **Nexperia**

N-channel 60 V 7.8 mΩ standard level MOSFET

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